Abstracts

A Large-Signal Model for the GaAs MESFET

A. Madjar and F.J. Rosenbaum. "A Large-Signal Model for the GaAs MESFET." 1981 Transactions on Microwave Theory and Techniques 29.8 (Aug. 1981 [T-MTT]): 781-788.

An analytic large-signal model for the GaAs FET is described which relates the terminal currents to the instantaneous terminal voltages and their time derivatives. It incorporates the device geometry and semiconductor parameters as well as the device parasitic circuit elements. The model is fast and efficient when implemented on a computer and is in a form suitable for large-signal circuit design and optimization.

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